

**Japanese Unexamined Patent Publication No.**

**200843/2004 (Tokukai 2004-200843)**

A. Relevance of the Above-identified Document

The following is a partial English translation of exemplary portions of non-English language information that may be relevant to the issue of patentability of the claims of the present application.

B. Translation of the Relevant Passage(s) of the Document

[CLAIMS]

[Claim 1]

A piezoelectric resonator element comprising:

a supporting film provided through an oscillation space formed on a substrate;

a lower electrode film formed on the supporting film;

a piezoelectric thin film formed on the lower electrode; and

an upper electrode film formed on the piezoelectric thin film,

the supporting film being made of aluminum nitride.

[Detailed Description of the Invention]

...

[Embodiment of the Invention]

...

[0018]

Although the piezoelectric thin film 5 is made of, for example, ZnO, AlN, CdS, PZT, or the like, ...

...

[0022]

Further, an AlN film is used as the supporting film 3 in the present embodiment. ...